HVQL20MB050D 2.0A 5.0kV

High Voltage Bridge Rectifier

INTRODUCE:

HVGT high voltage silicon Bridge rectifier is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. High reliability design.
2. High voltage design.
3. Power frequency ratio.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. Power transformer rectifier output.
2. Circuit rectification.
3. Power supply equipment.
4. Other.

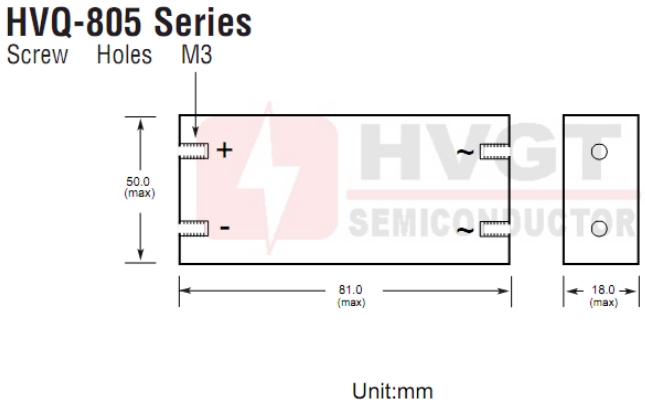
MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: built-in M3 nut.
3. Net weight: 120 grams (approx).

SHAPE DISPLAY:



SIZE: (Unit:mm) **HVGT NAME: HVQ-805**



Unit:mm

MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Renerse Voltage	V_{RRM}	@T_A=25°C	5.0	kV
Average Forward Current Maximum	I_{FAVM}	@T_A=55°C	2.0	A
Suege Current	I_{FSM}	@T_A=25°C; Half-Sine Wave; 8.3mS	30	A
Junction Temperature	T_J		125	°C
Allowable Operation Case Temperature	Tc		-40~+150	°C
Storage Temperature	T_{STG}		-40~+150	°C

ELECTRICAL CHARACTERISTICS: T_A=25°C (Unless Otherwise Specified)

Items	Symbols	Condition	Data Value	Units
Maximum Forward Voltage Drop	V_F	at 25°C; at I_{FAVM}	6.0	V
Maximum Reverse Current	I_R1	at 25°C; at V_{RRM}	5.0	uA
	I_R2	at 100°C; at V_{RRM}	30	uA
Maximum Reverse Recovery Time	T_{RR}	at 25°C; I_F=0.5I_R; I_R=I_{FAVM}; I_{RR}=0.25I_R	--	nS
Junction Capacitance	C_J	at 25°C; V_R=0V; f=1MHz	--	pF

Fig 1

Forward Current Derating Curve

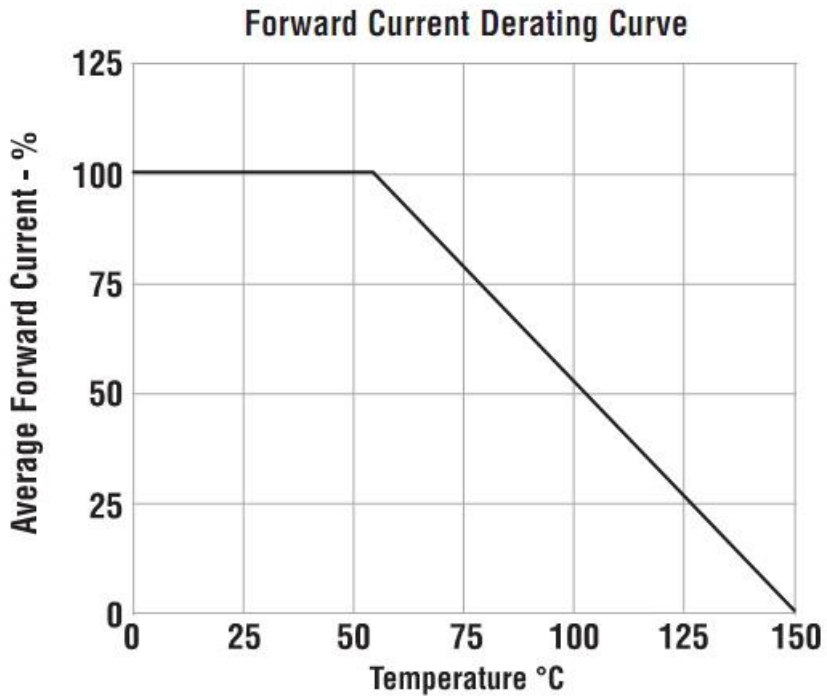


Fig 2

Non-Repetitive Surge Current

